Bourns®

- 1.5 A RMS
- Glass Passivated Wafer
- 400 V to 600 V Off-State Voltage
- Max I_{GT} of 10 mA
- Package Options

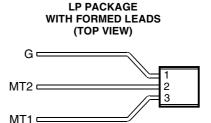
PACKAGE	PACKING	PART # SUFFIX		
LP	Bulk	(None)		
LP with fomed leads	Tape and Reel	R		



LP PACKAGE

MDC2AA

TICP206 SERIES SILICON TRIACS



MDC2AB

absolute maximum ratings over operating case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT	
Repetitive peak off-state voltage (see Note 1) TICP206D	VDRM	400 600	V	
Full-cycle RMS on-state current at (or below) 85°C case temperature (see Note 2)	T(RMS)	1.5	А	
Peak on-state surge current full-sine-wave at (or below) 25°C case temperature (see Note 3)	I _{TSM}	10	А	
Peak on-state surge current half-sine-wave at (or below) 25°C case temperature (see Note 4)	I _{TSM}	12	А	
Peak gate current	I _{GM}	±0.2	А	
Average gate power dissipation at (or below) 85°C case temperature (see Note 5)	P _{G(AV)}	0.3	W	
Operating case temperature range	T _C	-40 to +110	°C	
Storage temperature range	T _{stg}	-40 to +125	°C	
Lead temperature 1.6 mm from case for 10 seconds	TL	230	°C	

NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.

- 2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 85°C derate linearly to 110°C case temperature at the rate of 60 mA/°C.
- This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge
 may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
- 4. This value applies for one 50-Hz half-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
- 5. This value applies for a maximum averaging time of 20 ms.

electrical characteristics at 25°C case temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS			MIN	ТҮР	MAX	UNIT
I _{DRM}	Repetitive peak off- state current	V_D = rated V_{DRM}	I _G = 0				±20	μA
		V _{supply} = +12 V†	$R_L = 10 \Omega$	t _{p(g)} > 20 μs			8	
I _{GT}	Gate trigger	V _{supply} = +12 V†	$R_L = 10 \Omega$	t _{p(g)} > 20 μs			-8	mA
	current	V _{supply} = -12 V†	$R_L = 10 \Omega$	t _{p(g)} > 20 μs			-8	ШA
		V _{supply} = -12 V†	$R_L = 10 \Omega$	t _{p(g)} > 20 μs			10	
		V _{supply} = +12 V†	$R_L = 10 \Omega$	t _{p(g)} > 20 μs			2.5	V
V _{GT}	Gate trigger	V _{supply} = +12 V†	$R_L = 10 \Omega$	t _{p(g)} > 20 μs			-2.5	
	voltage	V _{supply} = -12 V†	$R_L = 10 \Omega$	t _{p(g)} > 20 μs			-2.5	v
		V _{supply} = -12 V†	$R_L = 10 \Omega$	t _{p(g)} > 20 μs			2.5	

† All voltages are with respect to Main Terminal 1.

PRODUCT INFORMATION

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electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

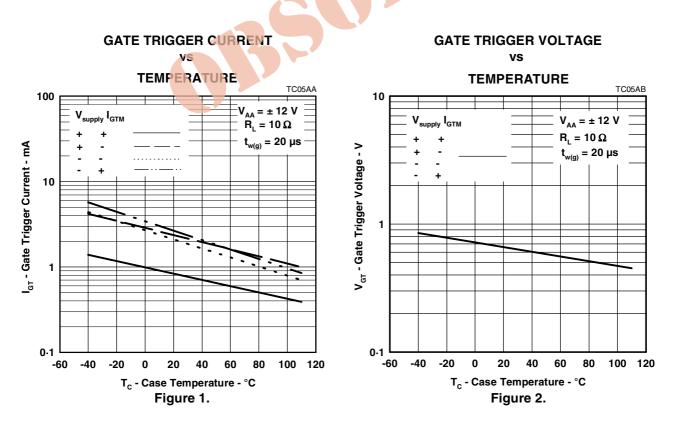
	PARAMETER TEST CONDITIONS			MIN	ТҮР	MAX	UNIT	
V _T	On-state voltage	$I_T = \pm 1 A$	l _G = 50 mA	(see Note 6)			±2.2	V
Ι _Η	Holding current	$V_{supply} = +12 V^{+}$ $V_{supply} = -12 V^{+}$	l _G = 0 l _G = 0	Init' I _{TM} = 100 mA Init' I _{TM} = -100 mA			30 -30	mA
ΙL	Latching current	V _{supply} = +12 V† V _{supply} = -12 V†	(see Note 7)				40 -40	mA

† All voltages are with respect to Main Terminal 1.

NOTES: 6. This parameter must be measured using pulse techniques, $t_p = \le 1$ ms, duty cycle ≤ 2 %. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

7. The triacs are triggered by a 15-V (open circuit amplitude) pulse supplied by a generator with the following characteristics: $R_G = 100 \Omega$, $t_{p(q)} = 20 \mu s$, $t_r = \le 15 ns$, f = 1 kHz.

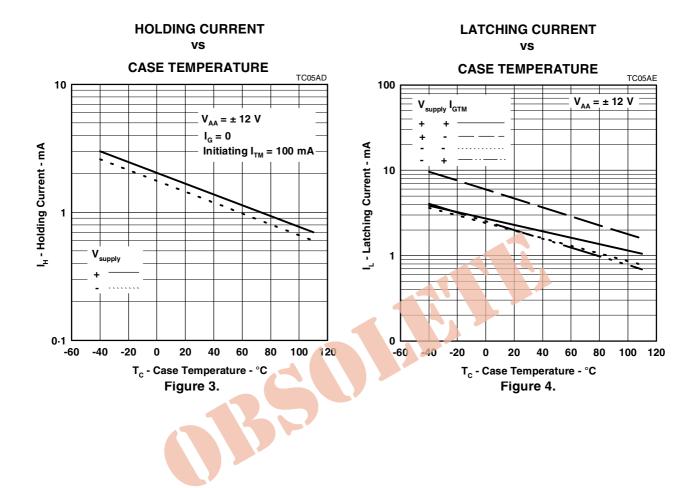




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TYPICAL CHARACTERISTICS



PRODUCT INFORMATION